Silicon PNP Power Transistors BD132

DESCRIPTION

·Complement to type BD131
·With TO-126 package
·High current (Max:- 3A)
·Low voltage (Max: -45V)

APPLICATIONS

·For general purpose power applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

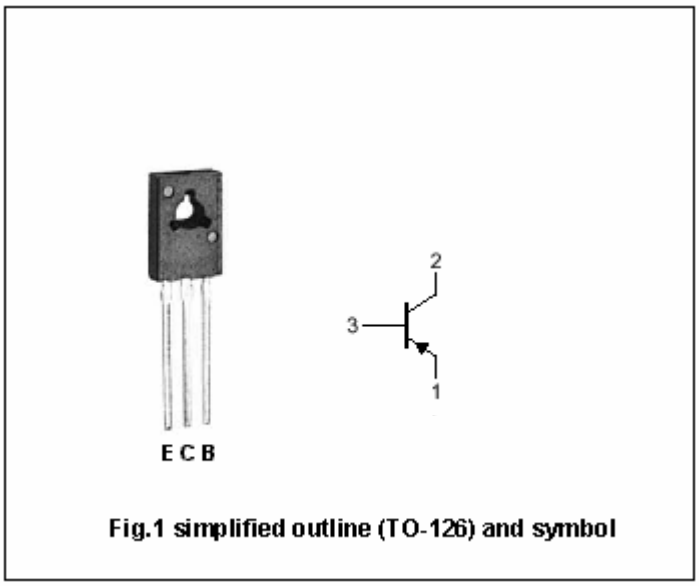

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-45	V
V_{CEO}	Collector-emitter voltage	Open base	-45	V
V_{EBO}	Emitter -base voltage	Open collector	-4	V
I_C	Collector current (DC)		-3	A
I_{CM}	Collector current-Peak		-6	A
I_{BM}	Base current-Peak		-0.5	A
P_t	Total power dissipation	T_{mb}≤60□	15	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-65~150	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}a}$	Thermal resistance from junction to ambient	100	K/W
$R_{th\ j\text{-}mb}$	Thermal resistance from junction to mounting base	6	K/W

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEsat-1}$	Collector-emitter saturation voltage	I_C=-0.5A; I_B=-50mA			-0.3	V
$V_{CEsat-2}$	Collector-emitter saturation voltage	I_C=-2A; I_B=-0.2A			-0.7	V
$V_{BEsat-1}$	Base-emitter saturation voltage	I_C=-0.5A; I_B=-50mA			-1.2	V
$V_{BEsat-2}$	Base-emitter saturation voltage	I_C=-2A; I_B=-0.2A			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-50V; I_E=0			-50	nA
		V_{CB}=-50V; I_E=0 T_j=150□			-10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-50	nA
h_{FE-1}	DC current gain	I_C=-0.5A ; V_{CE}=-12V	40			
h_{FE-2}	DC current gain	I_C=-2A ; V_{CE}=-1V	20			
f_T	Transition frequency	I_C=-0.25A; V_{CE}=-5V ;f=100MHz	60			MHz

PACKAGE OUTLINE

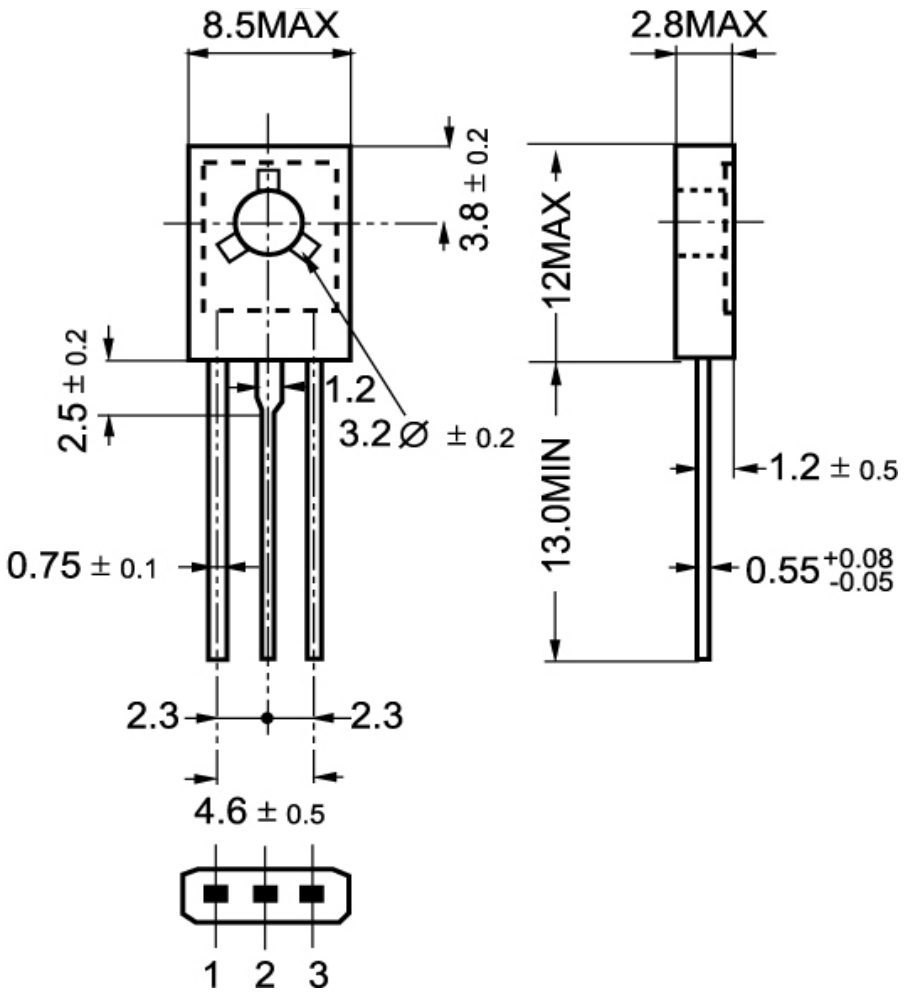

Fig.2 Outline dimensions